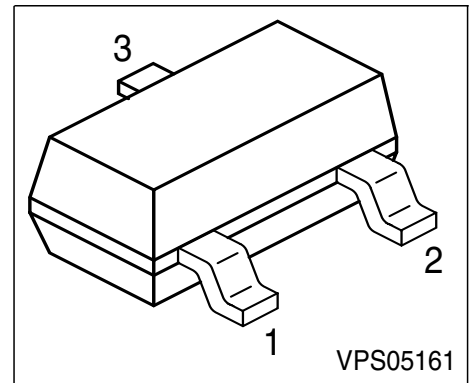
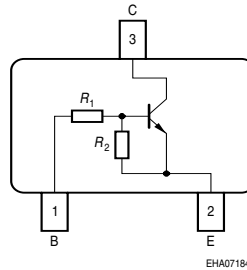


NPN Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1=10k\Omega$, $R_2=10k\Omega$)



Type	Marking	Pin Configuration			Package
BCR533	XCs	1 = B	2 = E	3 = C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Emitter-base voltage	V_{EBO}	10	
Input on Voltage	$V_{i(on)}$	50	
DC collector current	I_C	500	mA
Total power dissipation, $T_S = 79\text{ }^\circ\text{C}$	P_{tot}	330	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point ¹⁾	R_{thJS}	≤ 215	K/W
--	------------	------------	-----

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

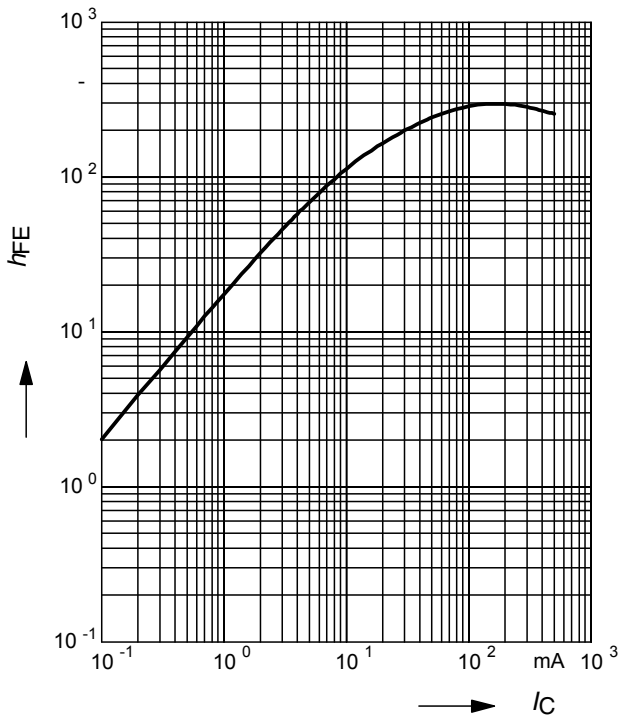
Electrical Characteristics at $T_A=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector cutoff current $V_{CB} = 40 \text{V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter cutoff current $V_{EB} = 10 \text{V}, I_C = 0$	I_{EBO}	-	-	0.75	mA
DC current gain 1) $I_C = 50 \text{mA}, V_{CE} = 5 \text{V}$	h_{FE}	70	-	-	-
Collector-emitter saturation voltage1) $I_C = 50 \text{mA}, I_B = 2.5 \text{mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{V}$	$V_{i(off)}$	0.6	-	1.5	
Input on Voltage $I_C = 10 \text{mA}, V_{CE} = 0.3 \text{V}$	$V_{i(on)}$	1.1	-	2.5	
Input resistor	R_1	7	10	13	k Ω
Resistor ratio	R_1/R_2	0.9	1	1.1	-
AC Characteristics					
Transition frequency $I_C = 50 \text{mA}, V_{CE} = 5 \text{V}, f = 100 \text{MHz}$	f_T	-	100	-	MHz

 1) Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

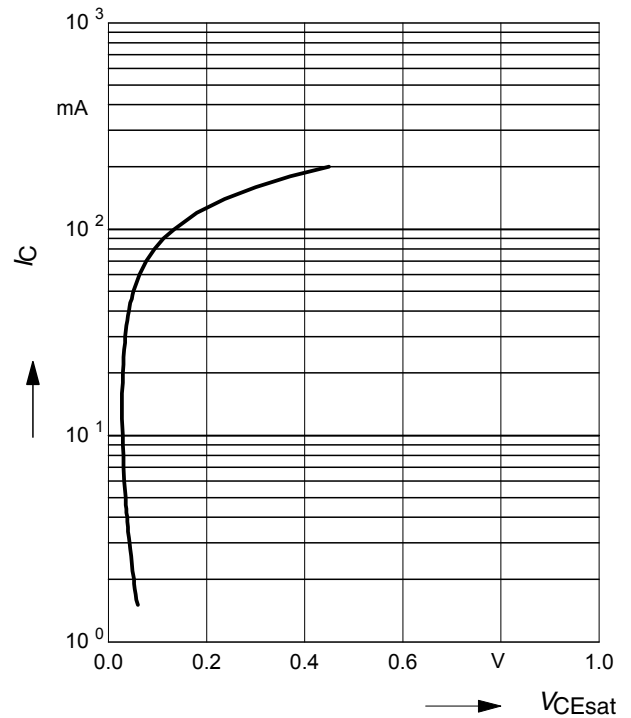
DC Current Gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



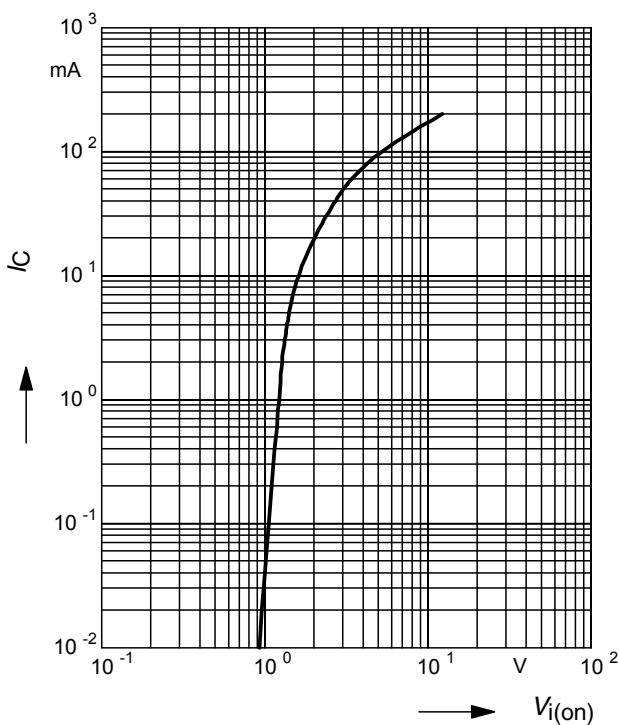
Collector-Emitter Saturation Voltage $V_{CEsat} = f(I_C), h_{FE} = 20$

$V_{CEsat} = f(I_C), h_{FE} = 20$



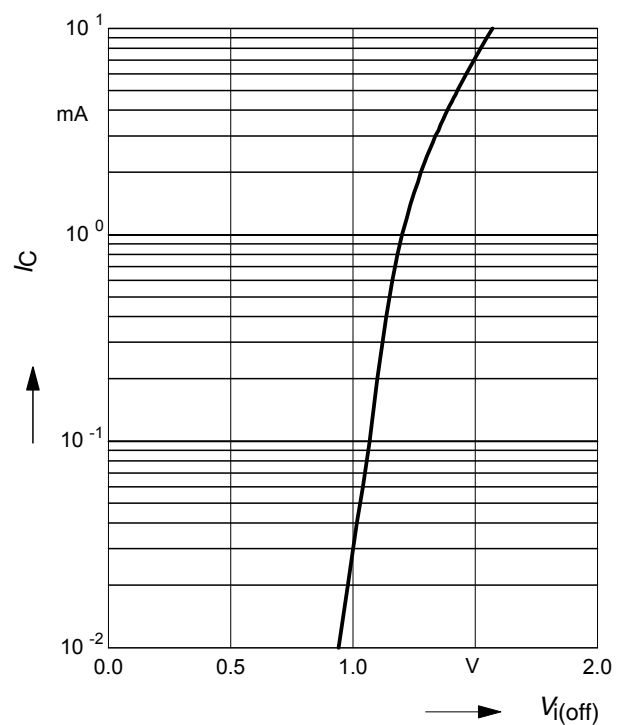
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$ (common emitter configuration)

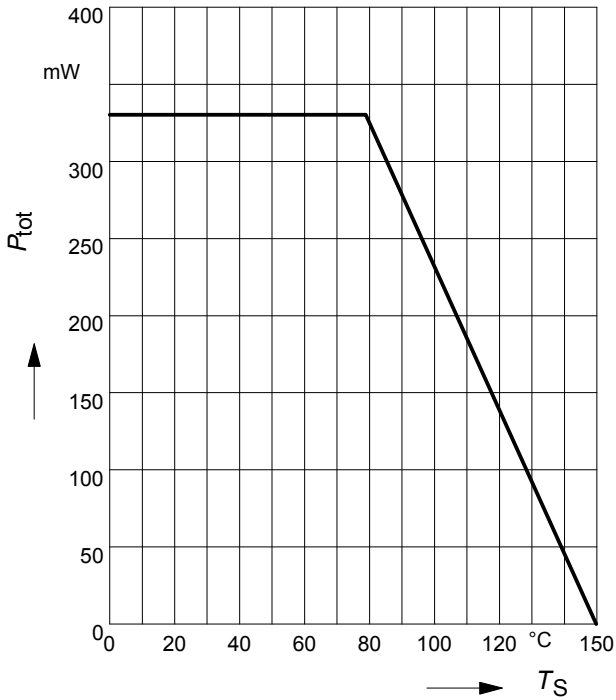


Input off voltage $V_{i(off)} = f(I_C)$

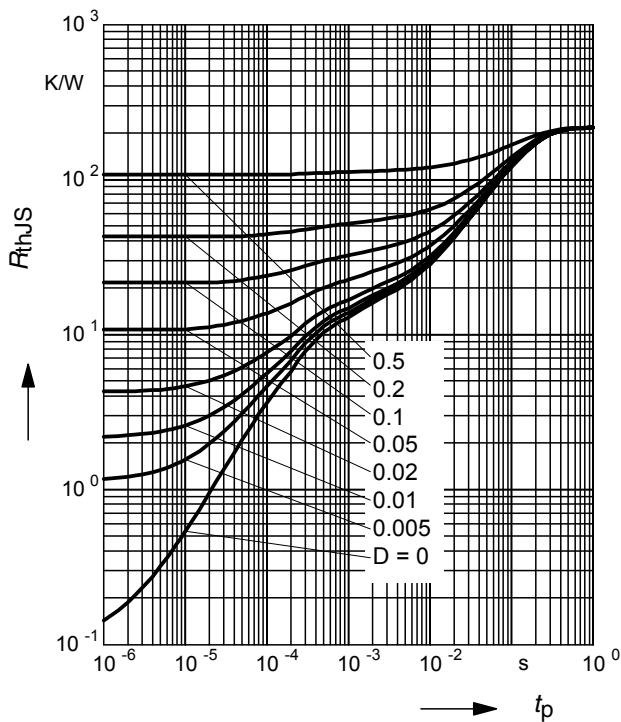
$V_{CE} = 5V$ (common emitter configuration)



Total power dissipation $P_{tot} = f(T_S)$

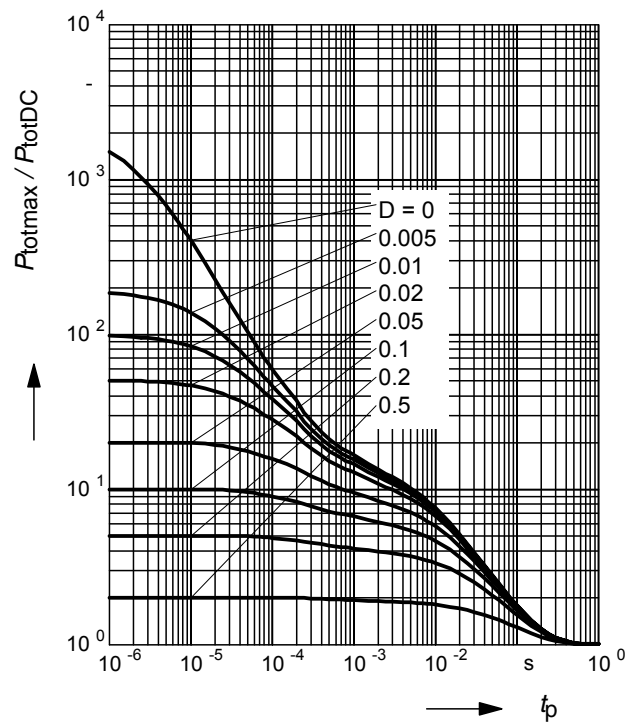


Permissible Pulse Load $R_{thJS} = f(t_p)$



Permissible Pulse Load

$P_{totmax} / P_{totDC} = f(t_p)$





LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.